



#### **40V DUAL NPN SMALL SIGNAL TRANSISTOR IN SOT363**

### **Features**

- BV<sub>CEO</sub> > 40V
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMDT2907A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

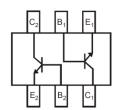
### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)

**SOT363** 



Top View



Device Schematic Top View

### **Ordering Information** (Note 4)

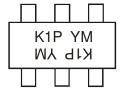
Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT2222A-7-F	Active	AEC-Q101	K1P	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

SOT363



K1P = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: D = 2016) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2013		2014	2015		2016	2017	'	2018	2019		2020
Code	Α		В	С		D	Е		F	G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{\sf CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Continuous Collector Current	lc	600	mA

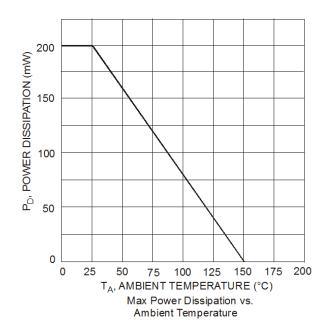
### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

## **Thermal Characteristic and Derating Information**



<sup>5.</sup> For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

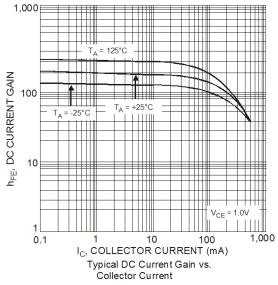
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$BV_{CBO}$	75		V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	$BV_{CEO}$	40		>	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0	_	V	$I_E = 100 \mu A, I_C = 0$
Collector-Base Cut-Off Current	I <sub>CBO</sub>		10	nA μA	$V_{CB} = 60V, I_E = 0$ $V_{CB} = 60V, I_E = 0, T_A = +150$ °C
Collector Cut-Off Current	I <sub>CEX</sub>		10	nA	$V_{CE} = 60V, V_{BE(OFF)} = 3.0V$
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	_	10	nA	V <sub>EB</sub> = 3V, I <sub>C</sub> = 0
Base Cutoff Current	I <sub>BL</sub>		20	nA	$V_{CE} = 60V, V_{BE(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h <sub>FE</sub>	35 50 75 100 40 50 35	 300  		$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 10V \\ I_C &= 1.0 m A, \ V_{CE} = 10V \\ I_C &= 150 m A, \ V_{CE} = 10V \\ I_C &= 150 m A, \ V_{CE} = 10V \\ I_C &= 500 m A, \ V_{CE} = 10V \\ I_C &= 10 m A, \ V_{CE} = 10V, \ T_A = -55^{\circ}C \\ I_C &= 150 m A, \ V_{CE} = 1.0V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.3 1.0	٧	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.6	1.2 2.0	>	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
SMALL SIGNAL CHARACTERISTICS				•	
Output Capacitance	Cobo	_	8.0	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Input Capacitance	Cibo	_	25	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Current Gain-Bandwidth Product	f <sub>T</sub>	300		MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 100MHz
Noise Figure	N <sub>F</sub>		4.0	dB	$V_{CE} = 10V, I_{C} = 100\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>D</sub>	_	10	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t <sub>R</sub>		25	ns	$V_{BE(OFF)} = -0.5V$ , $I_{B1} = 15mA$
Storage Time	ts		225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,
Fall Time	t <sub>F</sub>	_	60	ns	$I_{B1} = I_{B2} = 15mA$

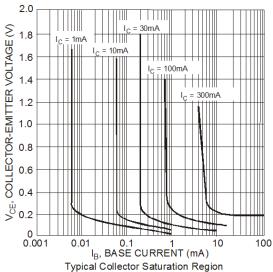
Note:

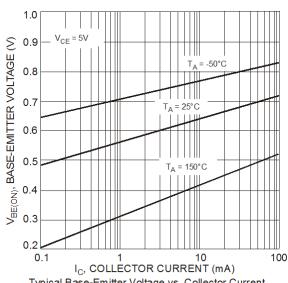
7. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s.$  Duty cycle  $\leq 2\%.$ 

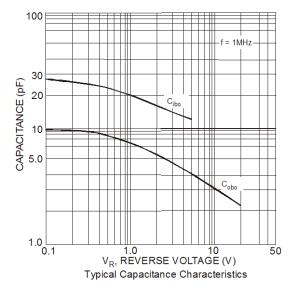


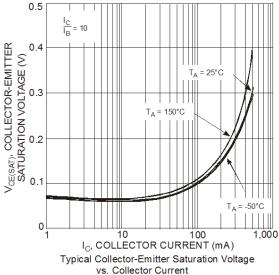
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)











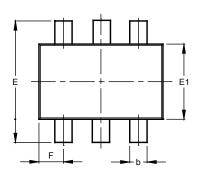
Typical Base-Emitter Voltage vs. Collector Current

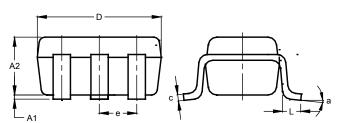


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



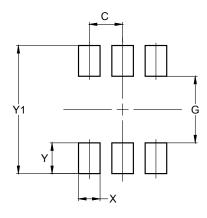


SOT363						
Dim	Min	Max	Тур			
<b>A</b> 1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### **SOT363**



Dimensions	value
Dilliensions	(in mm)
С	0.650
G	1.300
X	0.420
Υ	0.600
Y1	2.500



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